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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Ohtani, et al. Art Unit : 2815
Serial No. : 09/455,991 Examiner : Jose R. Diaz
Filed : December 6, 1999 Confirmation No.: 5835
Title : METHOD OF MANUFACTURING A SEMICONDUCTOR DEVICE HAVING
TFTS WITH UNIFORM CHARACTERISTICS (AS AMENDED)

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Commissioner for Patents
P.O. Box 1450
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REPLY TO ACTION OF MARCH 21, 2005

In reply to the Final Office Action of March 21, 2005, applicants submit the following remarks.

Claims 6-12, 14-16, 18, 20, 21 and 23-79 are pending, with claims 6, 9, 24, 31, 40, 48, 55 and 64 being independent. Claims 1-5, 13, 17, 19, and 22 were previously cancelled without prejudice or disclaimer.

The claims have been rejected as being anticipated by Zhang (U.S. Patent No. 5,922,125). With respect to claim 6 and its dependent claims, applicant again requests reconsideration and withdrawal of this rejection because Zhang does not describe or suggest "crystallizing the amorphous semiconductor film from the first metal element added region and the second metal element added region *in parallel to the substrate to form* a first crystalline portion and *a second crystalline portion*, respectively, in a crystalline semiconductor film."

In response to this argument, the office action states that "Zhang explicitly teaches the new limitation of growing crystals in directions parallel to the substrate (see abstract, and arrows (104) to (107) in figure 1B)." Applicant notes that, though Fig. 1B of Zhang shows the arrows 105 and 106 moving away from region 109, this is clearly an error in the figure, since it is inconsistent both with Figs. 1A and 2, and with the text of the application describing Fig. 1B. In particular, Figs. 1A and 2 clearly show the arrows 105 and 106 pointing toward the region 109. As stated in Zhang at col. 4, lines 34-38 (emphasis added): "The growth of crystals as indicated by arrows 104 to 107 in FIG. 1(A) is carried out in directions parallel to the substrate 11 *from the regions 101 and 102* where nickel is held in contact with the surface of the amorphous